

EVAL-1ED020I12F2-DB user guide

Isolated driver daughter board to evaluate 1200 V CoolSiC™ MOSFET

About this document

Scope and purpose

This user guide explains how to operate the evaluation board “EVAL-1ED020I12F2-DB” (daughterboard) together with the “Evaluation platform 1200V CoolSiC™ MOSFET in TO247 3pin / 4pin Rev. 2.” (motherboard)

Intended audience

This document is intended for owners and users of the evaluation board.

Evaluation Board

This board is to be used during design-in tasks, for evaluation and measurement of product characteristics, and proof of data sheet specifications.

Note: PCB and auxiliary circuits are NOT optimized for final customer design.

Important notice

Important notice

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Safety precautions

Safety precautions

Note: Please note the following warnings regarding the hazards associated with development systems.

Table 1 Safety precautions

| | |
|---|---|
|  | Warning: The DC link potential of this board is up to 1200 V _{DC} . When measuring voltage waveforms by oscilloscope, high voltage differential probes must be used. Failure to do so may result in personal injury or death. |
|  | Warning: The evaluation or reference board contains DC bus capacitors which take time to discharge after removal of the main supply. Before working on the drive system, wait five minutes for capacitors to discharge to safe voltage levels. Failure to do so may result in personal injury or death. Darkened display LEDs are not an indication that capacitors have discharged to safe voltage levels. |
|  | Warning: The evaluation or reference board is connected to the grid input during testing. Hence, high voltage differential probes must be used when measuring voltage waveforms by oscilloscope. Failure to do so may result in personal injury or death. Darkened display LEDs are not an indication that capacitors have discharged to safe voltage levels. |
|  | Warning: Remove or disconnect power from the drive before you disconnect or reconnect wires, or perform maintenance work. Wait five minutes after removing power to discharge the bus capacitors. Do not attempt to service the drive until the bus capacitors have discharged to zero. Failure to do so may result in personal injury or death. |
|  | Caution: The heat sink and device surfaces of the evaluation or reference board may become hot during testing. Hence, necessary precautions are required while handling the board. Failure to comply may cause injury. |
|  | Caution: Only personnel familiar with the drive, power electronics and associated machinery should plan, install, commission and subsequently service the system. Failure to comply may result in personal injury and/or equipment damage. |
|  | Caution: The evaluation or reference board contains parts and assemblies sensitive to electrostatic discharge (ESD). Electrostatic control precautions are required when installing, testing, servicing or repairing the assembly. Component damage may result if ESD control procedures are not followed. If you are not familiar with electrostatic control procedures, refer to the applicable ESD protection handbooks and guidelines. |
|  | Caution: A drive that is incorrectly applied or installed can lead to component damage or reduction in product lifetime. Wiring or application errors such as undersizing the motor, supplying an incorrect or inadequate AC supply, or excessive ambient temperatures may result in system malfunction. |
|  | Caution: The evaluation or reference board is shipped with packing materials that need to be removed prior to installation. Failure to remove all packing materials that are unnecessary for system installation may result in overheating or abnormal operating conditions. |

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The board at a glance

1 The board at a glance

The evaluation board “**EVAL-1ED020I12F2-DB**” is part of the CoolSiC™ evaluation platform second revision. This platform was developed to show the optimal driving of the silicon carbide CoolSiC™ MOSFETs or other power switches in TO247 3-pin or 4-pin package. To achieve this target the design was split in two boards, one motherboard (evaluation platform) “**EVAL-PS-DP-MAIN**” and a flexible driver-card, e.g. (evaluation board “**EVAL-1ED020I12F2-DB**”). The modular approach enables future expansion of the platform with additional gate driver cards. This means, the driver card is connected to the motherboard via connectors. In this way it is possible to have different driver cards with of course different drivers which can work with one motherboard. The power switches can be connected via connectors as well.

The first driver card, based on the evaluation platform second revision, contains the EiceDRIVER™ IC 1ED020I12-F2 with an integrated active Miller clamp preventing unintended turn-on and a DESAT pin to protect the application against damage through short circuit.

Figure 1 and Figure 2 shows the daughterboard EVAL-1ED020I12F2-DB, Figure 3 shows the CoolSiC™ evaluation platform.

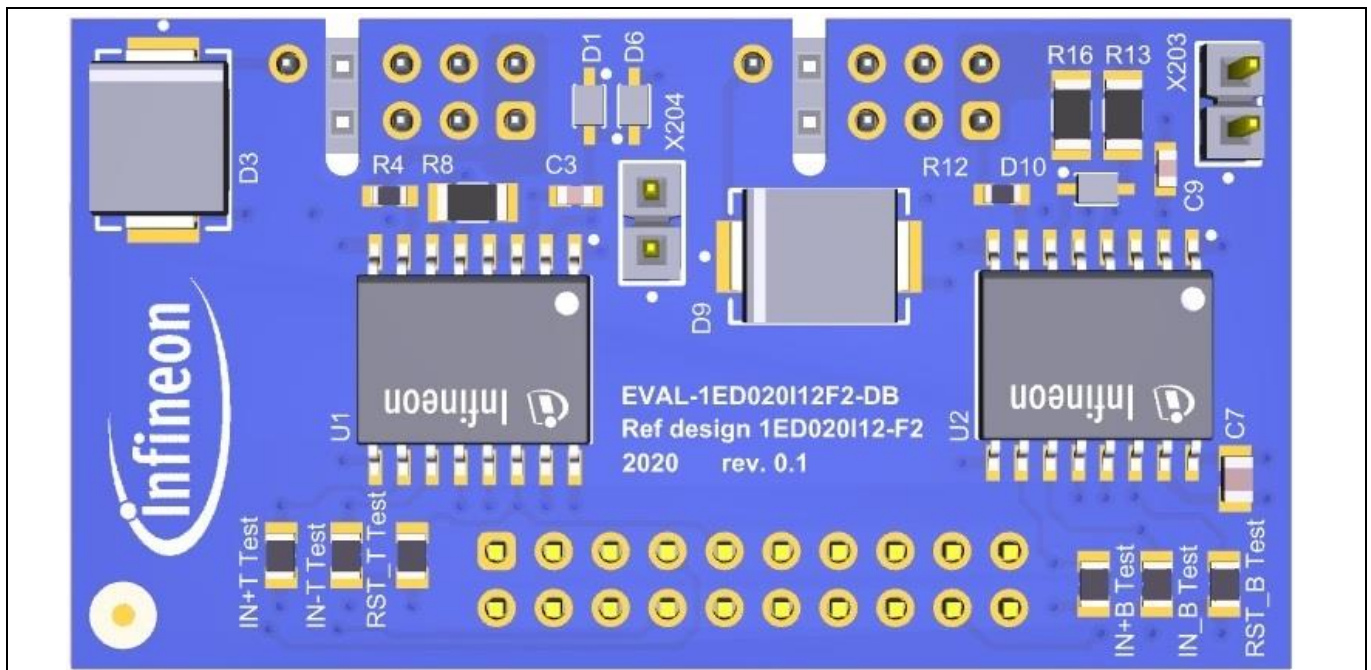


Figure 1 Top view of evaluation daughterboard EVAL-1ED020I12F2-DB

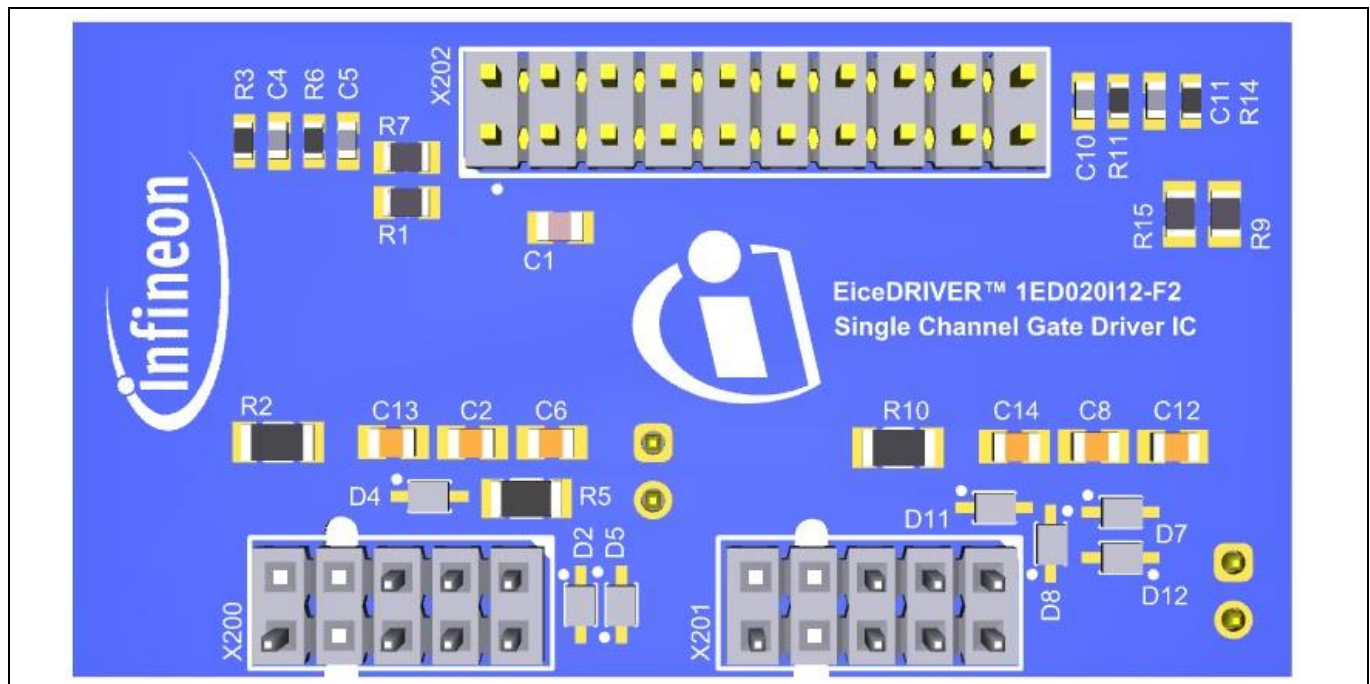


Figure 2 Bottom view of evaluation daughterboard EVAL-1ED020I12F2-DB

A more detailed description please see in Chapter 1.2.

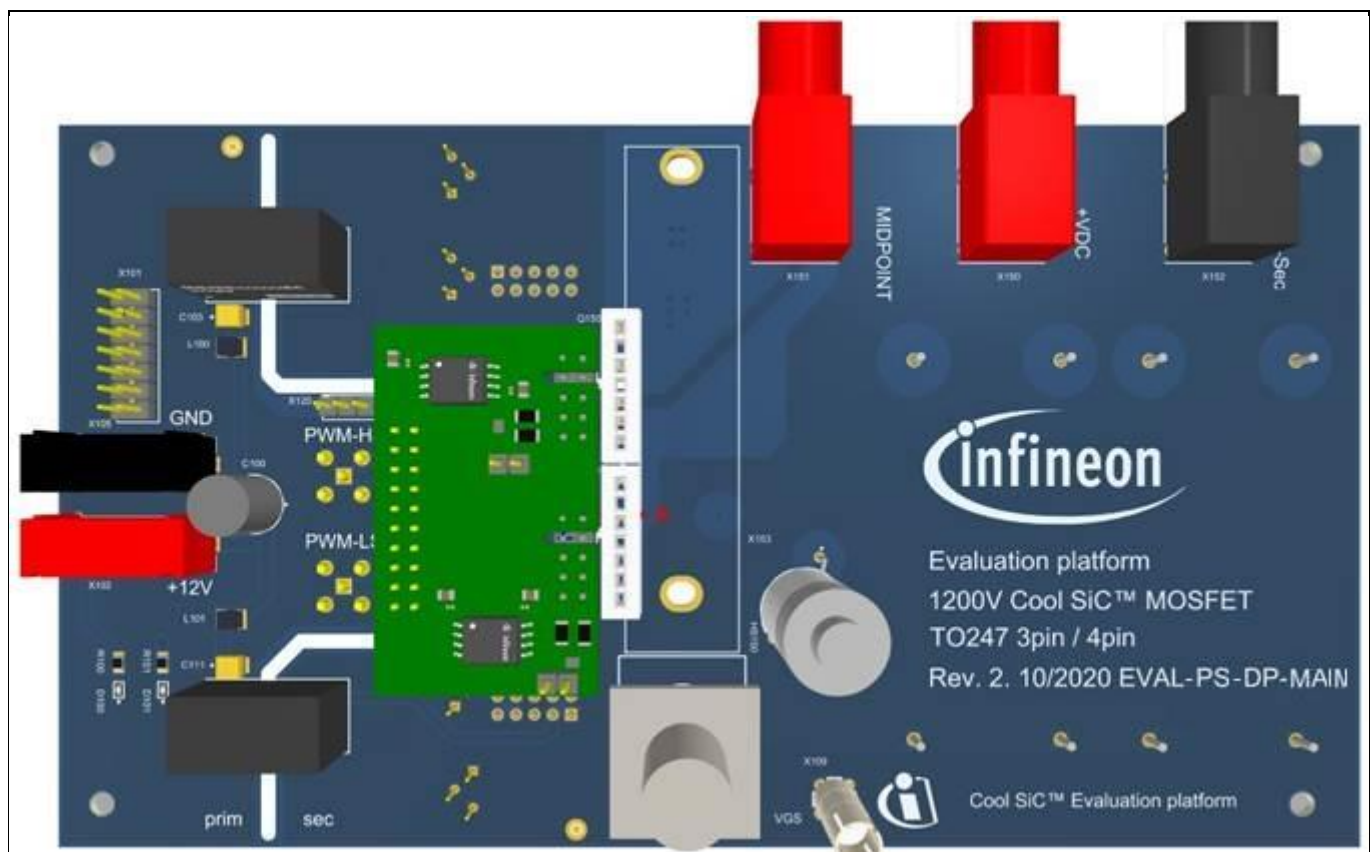


Figure 3 Top view complete solution (motherboard + daughterboard)

The board at a glance

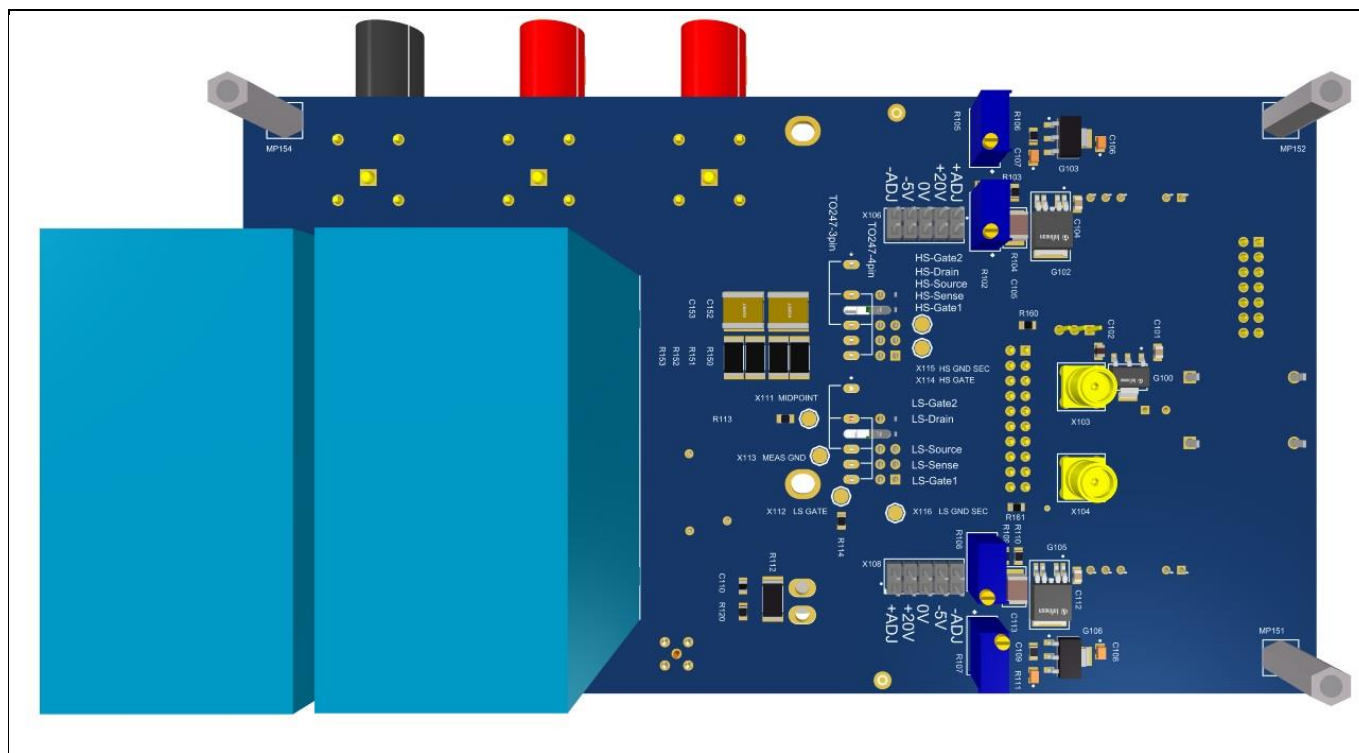


Figure 4 Bottom view motherboard

1.1 Delivery content

Content of delivery is the EVAL-1ED020I12F2-DB board packed in a box. The evaluation platform EVAL-PS-DP-MAIN can be ordered separately. Since different daughterboards, such as EVAL-1ED020I12F2-DB, can be driven with one evaluation platform (motherboard), this arrangement allows a flexible choice of daughterboards with the motherboard.

1.2 Block diagram

The block diagram of the EVAL-1ED020I12F2-DB board is depicted in Figure 5.

The board at a glance

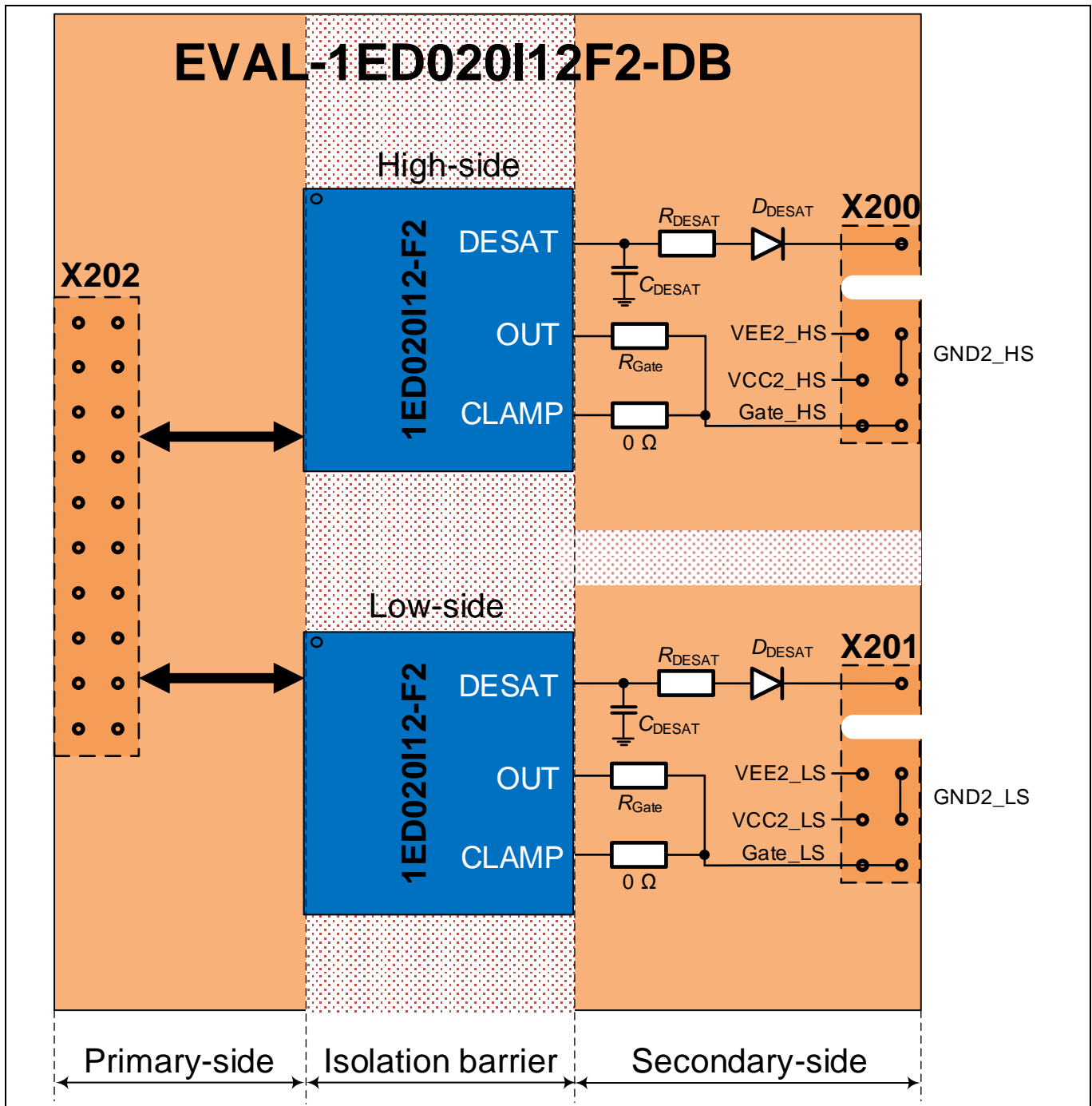


Figure 5 Blockdiagramm of EVAL-1ED020I12F2-DB

The connector X202 (see Figure 5) connects the daughter board with all signals from the primary side (low-voltage side) of the gate driver, like IN+, IN-, /Fault, /RDY, VCC1 and GND1 of both drivers to the evaluation platform and the corresponding connector X100 on this platform

As interface to the power switches acting the connectors X200 and X201 (see Figure 5) with the gate signal, the source connection and the drain connection for the DESAT function. Connector X200 serves the high-side switch, X201 the low-side switch. At the same time, the respective supply voltages for the drivers (VCC2, VEE2 and GND2) are connected.

The board at a glance**1.3 Main features**

- Two separate single-channel isolated gate driver
- Each driver has 2.4 A rail-to-rail outputs
- For 600 V / 1200 V power switches, like MOSFETs, IGBTs or SiC MOSFETs
- DESAT-detection for overcurrent / short-circuit protection
- Active Miller clamp

1.4 Board parameters and technical data

The key specifications of this board are displayed in Table 2.

Table 2 Parameter

| Parameter | Symbol | Value (max) | Unit | Test condition |
|--|--------|-------------|------|-----------------|
| Positive power supply output side | VCC2 | 20 | V | ¹⁾ |
| Negative power supply output side | VEE2 | -12 | V | ¹⁾ |
| Maximum power supply voltage output side (VCC2 – VEE2) | Vmax2 | 28 | V | |
| Positive power supply input side | VCC1 | 6.5 | V | |
| Input-to-output isolation voltage | VISO | 1200 | V | |
| Gate driver high output maximum current (per channel) | IOUT | 2.4 | A | t = 2 μs |
| Gate & clamp driver low output maximum current (per channel) | IOUT | 2.4 | A | t = 2 μs |
| Mechanical dimensions | length | 54 | mm | |
| | width | 29 | mm | |
| | height | 19 | mm | With connectors |

¹⁾ With respect to GND2

All this technical electrical parameter shown in Table 2 are related to the Infineon gate driver IC 1ED020I12-F2.

2 System and functional description

2.1 Use of the daughterboard

The daughter board can be used in two different ways.

- 1.) Stand-alone board
- 2.) Usage together with motherboard

2.1.1 Stand-alone board

In the case of stand-alone usage, the application is structured in such a way that the following must be developed: circuit board with corresponding plug connectors, galvanically isolated power supplies, connections for the high-voltage power switches, and the connections for the low voltage side. The technical parameters in Table 2 have to be considered. Please also note that there is an insulation gap between the low voltage and the high voltage side, as shown in Figure 5.

2.1.2 Usage together with motherboard

If the motherboard, EVAL-PS-DP-MAIN, is used, commissioning is simple, as the daughterboard was specifically designed to be used together with it. Figure 3 shows the top view of this motherboard.

Please read the data sheet for the motherboard before starting up.

The motherboard is divided into two sections: the primary supply side on the left and the power (high-voltage) circuit indicated as secondary side on the right. They are separated by the white marker line. On the primary side, four connectors are visible: X105, X102, X101 and X100. The 12 V supply voltage on the low-voltage side is connected (red-colored, positive pole) to X102 and X105. Three other voltages for the two drivers are generated from this 12 V power supply: VCC1, VCC2 and VEE2.

VCC2 and VEE2 are galvanically separated from each other and also from the other voltages.

The connector X100 connect the primary side of the mainboard and the primary side of the EVAL-1ED020I12F2-DB which each other. All important signals from EVAL-1ED020I12F2-DB like IN+, IN-, /Fault and /RDY of both drivers will be provided via X100 from the motherboard to the EVAL-1ED020I12F2-DB. At the motherboard side this signals are delivered from connector X101, which is the interface to the outside world, for example a μ Controller.

The EVAL-1ED020I12F2-DB is supplied with supply voltages VCC1, VCC2 and VEE2 via DC/DC converters. These connectors are mounted on the motherboard and enable a flexible supply. The decision about which driving voltages (VCC2 and VEE2) are to be connected to the EVAL-1ED020I12F2-DB via connectors X107 and X110 is made via jumpers on the pin headers X108 (low-side) and X106 (high-side). VCC1 is provided via connector X100.

The power supply can be configured with two jumpers on the high-side and two jumpers on the low-side according to the requirements of the drivers at the EVAL-1ED020I12F2-DB or other daughterboards and the downstream power switches.

The possible configurations for setting the driving voltages (VCC2 and VEE2) via two jumpers are visualized in Table 3 and Figure 6.

EVAL-1ED020I12F2-DB user guide

Isolated driver daughter board to evaluate 1200 V CoolSiC™ MOSFET

System and functional description

Table 3 Jumper configurations for powersupply of EVAL-1ED020I12F2-DB

| +ADJ | +20V | 0V | -5V | -ADJ |
|------|------|----|-----|------|
| X | | X | | |
| X | | | X | |
| X | | | | X |
| | X | X | | |
| | X | | X | |
| | X | | | X |

The settings for the adjustable driver voltages are made using the potentiometer R105 and R102 for the high-side driver and with potentiometer R108 and R107 for the low-side driver of the EVAL-1ED020I12F2-DB. R102 and R106 adjust the positive voltage (VCC2) of the drivers in the range between 7.5 V and +20V, R105 and R107 adjust the negative voltage (VEE2) in the range between -1 V and -4.5 V.

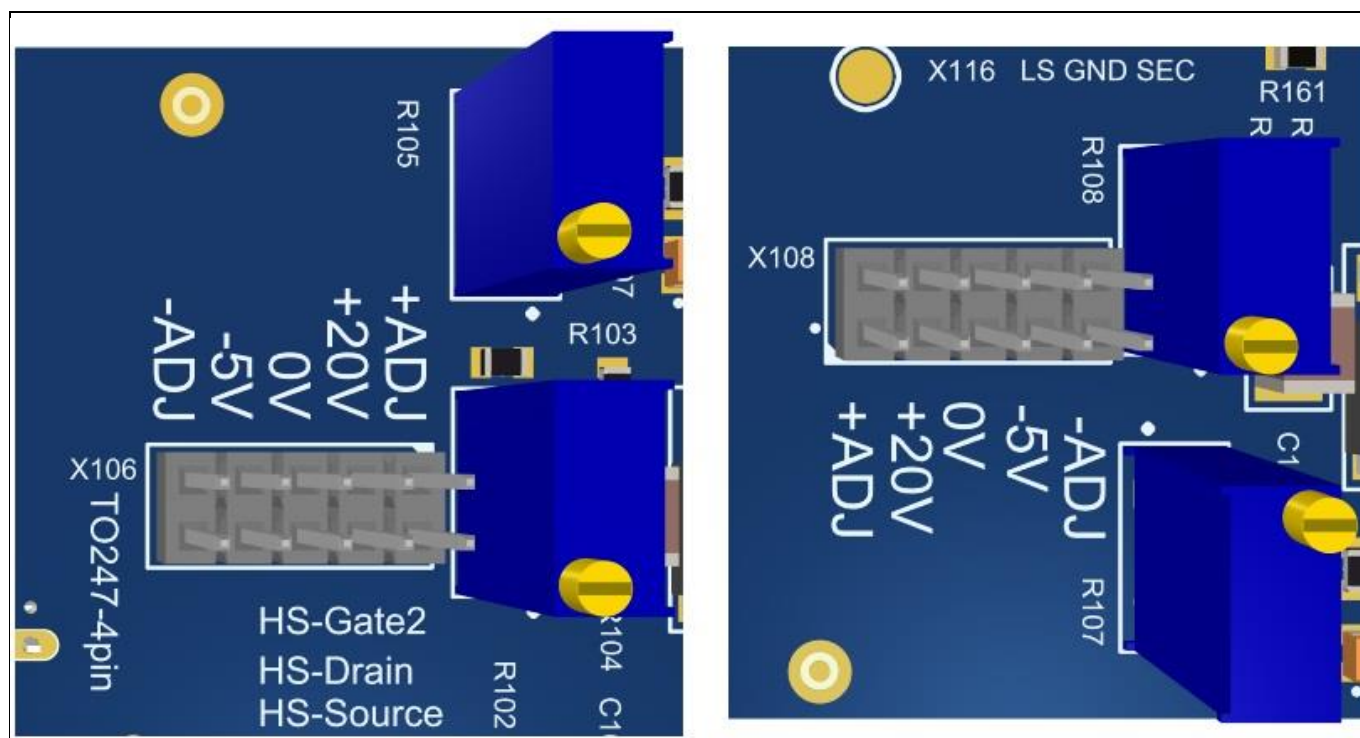


Figure 6 Jumper and potentiometer for voltage settings VCC2 and VEE2

2.2 Description of the functional blocks

The description of the functional blocks of the daughterboard EVAL-1ED020I12F2-DB refer to Figure 5. All connections are shown only roughly, the detailed circuit is shown in Figure 8.

In principle, the board can be separated into two parts, the primary and the secondary side. The primary side describes the low voltage area, the secondary the high-voltage area, which directly controls the power switch. No components or electrical lines should be placed in the isolation barrier, as otherwise the insulation between input and output (primary and secondary side) cannot be guaranteed.

Furthermore, two gate driver ICs, 1ED020I12-F2, which can generally be operated separately, are positioned on the board. In connection with the motherboard, this two drivers working in a half-bridge configuration, so that one IC works as the high-side driver and the other IC as the low-side driver.

The primary side comprises the connector X202 as well as all necessary lines and passive components which are necessary for the safe operation of the gate drivers. Connector X202 delivers all the necessary control signals (IN+, IN-, /FLT, RDY and /RST) as well as the electrical power (VCC1 and GND1) to the primary side of both gate driver ICs. More detailed information can be found in Chapter 4.4, Table 5.

The connectors X200 and X201 on the secondary side are used to supply the two drivers with the secondary power supply which is required for the gate voltages and are the connection to the power switches. Each gate driver has its own power supply, they are galvanically isolated to each other. More detailed information about the connectors X200 and X201 can be found in Chapter 4.4, Table 6 and Table 7.

Via R_{DESAT} , D_{DSAT} and X200-10/X201-10, the DESAT inputs of the gate drivers are connected to the drain when used with of SiC MOSFET or MOSFET, or to the Collector when used with IGBT. This DESAT function protects the power switches against over current situations.

The outputs “OUT” of the gate drivers are connected via R_{Gate} and X200-1,2/X201-1,2 to the gate of the corresponding power switch and delivers the gate voltage to drive the power switches.

Outputs “CLAMP” are connected via zero ohm resistors (0 Ω) to the gate resistors. The reason is, if clamp function is not required, resistors just can be removed.

2.2.1 Basic operation

Please note that the entire evaluation platform was designed for double-pulse tests and short-circuit tests only. The evaluation platform is unsuitable for long-term tests, as the power switches are not soldered. Figure 7 presents a possible configuration of this combination of mother- and daughterboard.

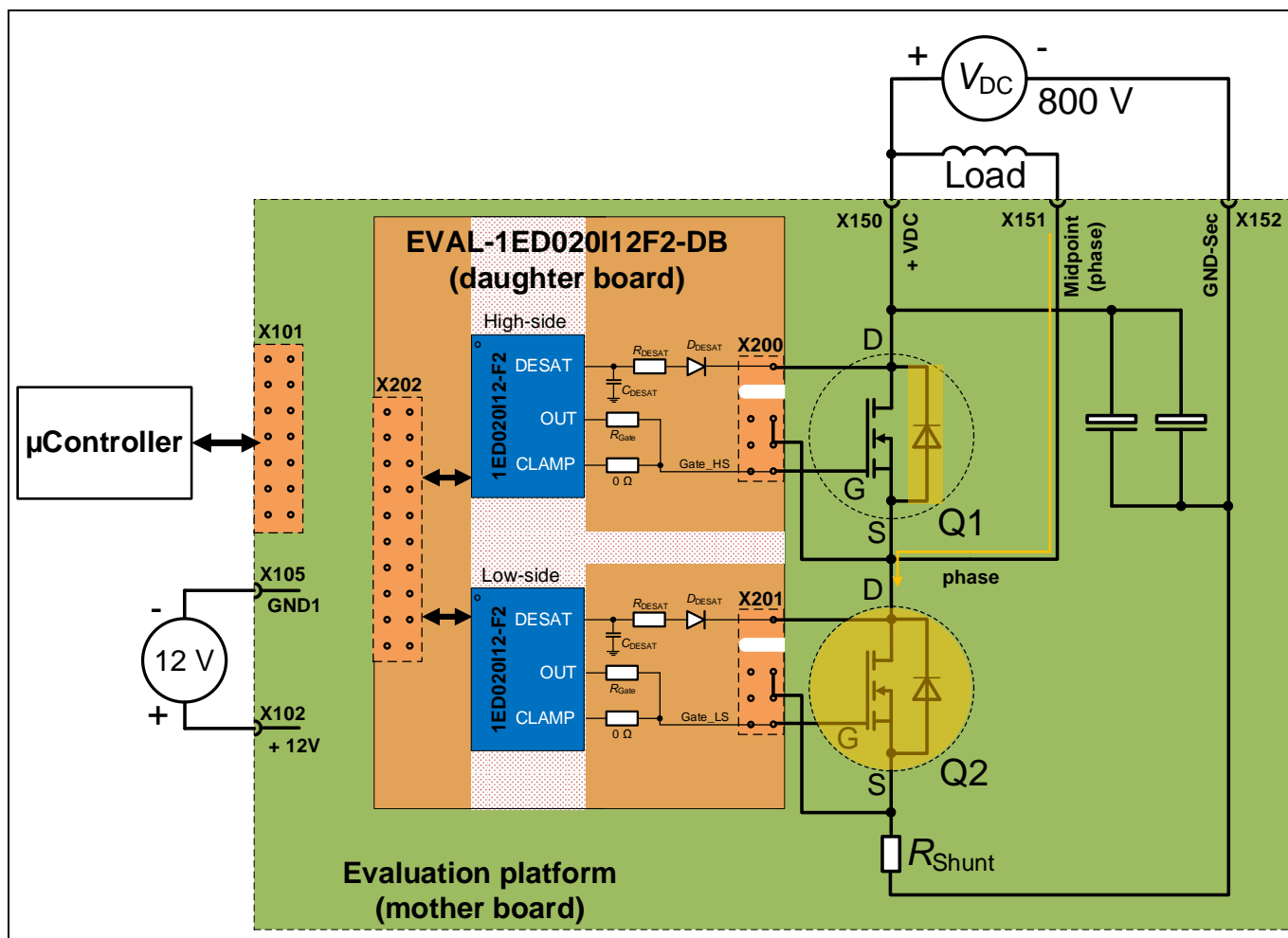


Figure 7 Motherboard equipped with daughterboard and SiC MOSFET's for low-side measurements

Especially in this configuration (wiring of the load) the arrangement can be used for low-side measurements. Power switch Q2 is now the DUT (device under test).

A configuration for high-side measurements is shown in Chapter 4.1.3.

2.2.2 First steps for start up

Before the whole application can be put into operation, the following commissioning steps should be observed:

- 1.) Take empty motherboard out of the box
- 2.) Connect 12 V corresponding to Figure 7
- 3.) Set the jumpers for driver voltages as described in Chapter 2.1.2, Table 3 and Figure 6, according to the needs of the corresponding drivers at the daughterboard
- 4.) If an adjustable powersupply has been selected, VCC2 and VEE2 has to be set by the potentiometer according to details described in Chapter 2.1.2, Table 3 and Figure 6
- 5.) Disconnect 12 V (to make all changes without power supply)
- 6.) Plugging in the daughterboard and the power switches
- 7.) Connect 12 V and μ Controller interface (or other 5 V-compatible digital switching signals) to connector X101 (see Figure 7)
- 8.) Connect the high-voltage power supply (ensure that it is switched off !!) and load according to the requirements

Now the complete setup (motherboard + daughterboard) is ready for testing. If all safety conditions applicable to the respective laboratory are complied with, the high voltage can be switched on and measurements can be started.

System design

3 System design

3.1 Schematics

Figure 8 shows the drawing of the daughterboard 1ED020I12F2-DB.

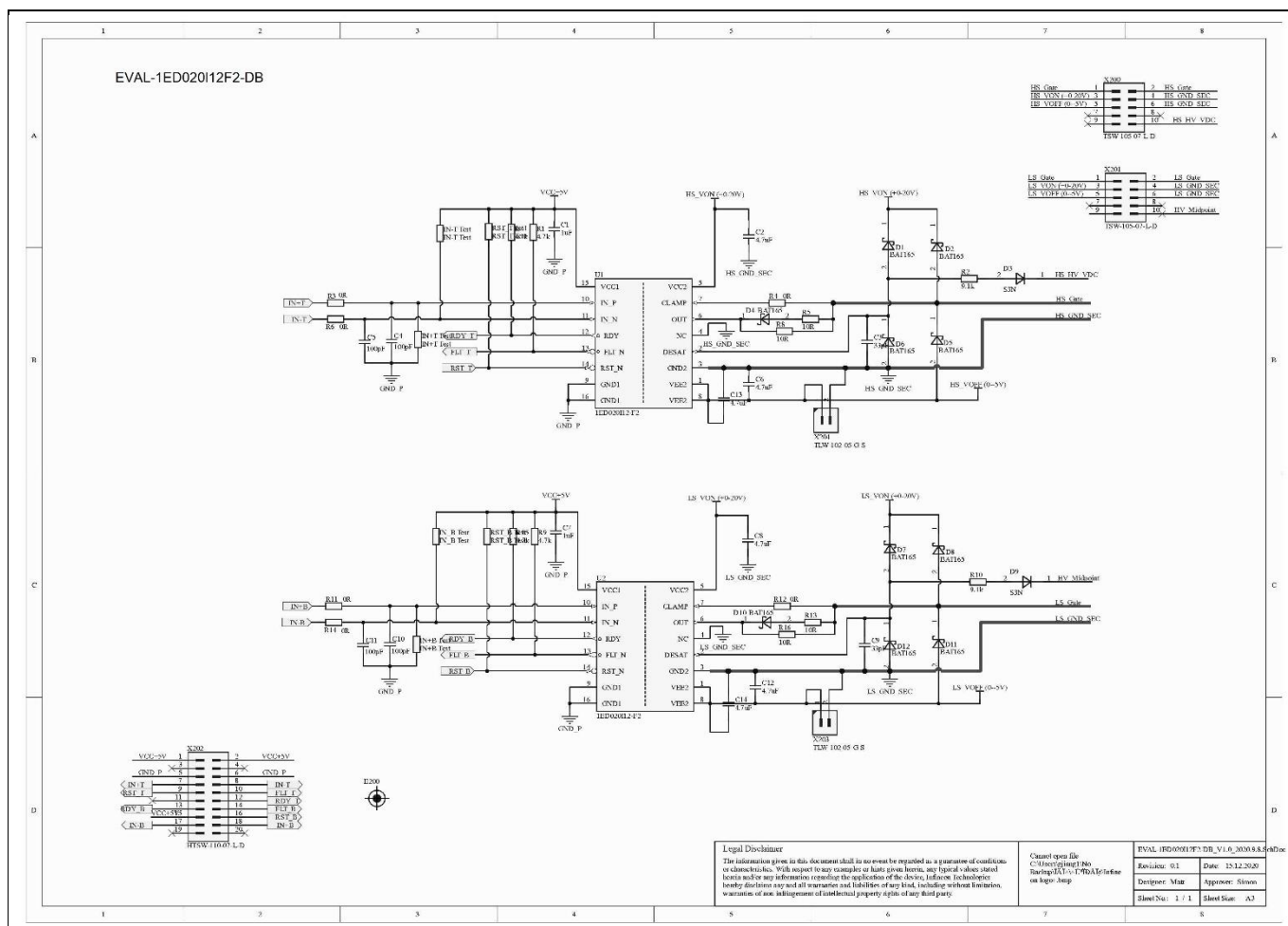


Figure 8 Drawing of EVAL-1ED020I12F2-DB

3.2 Layout

The following figures present the different layers of the layout from the daughterboard EVAL-1ED020I12F2-DB. Due to the small dimensions of the design, a 4-layer layout was provided. The order from the top view: Top layer, Layer 1, Layer 2, Bottom layer

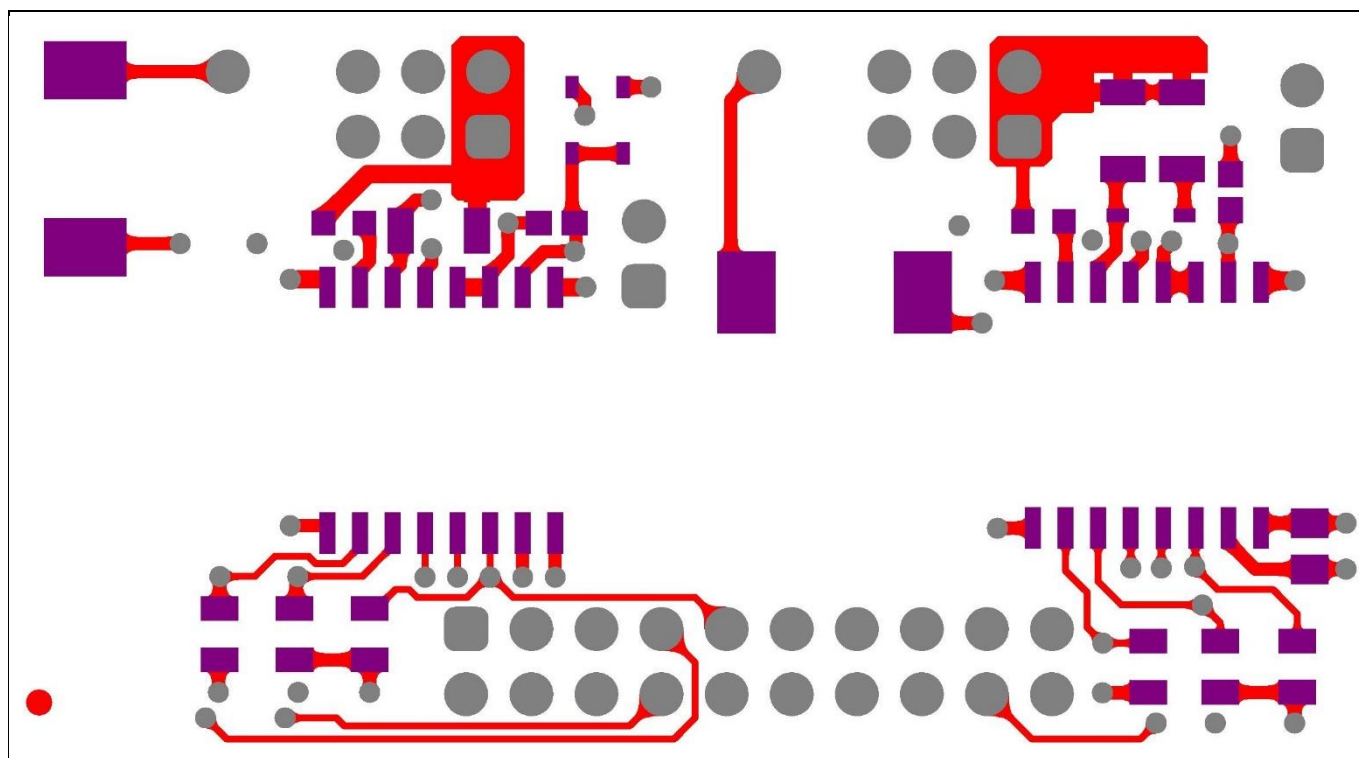


Figure 9 Top layer of EVAL-1ED020I12F2-DB

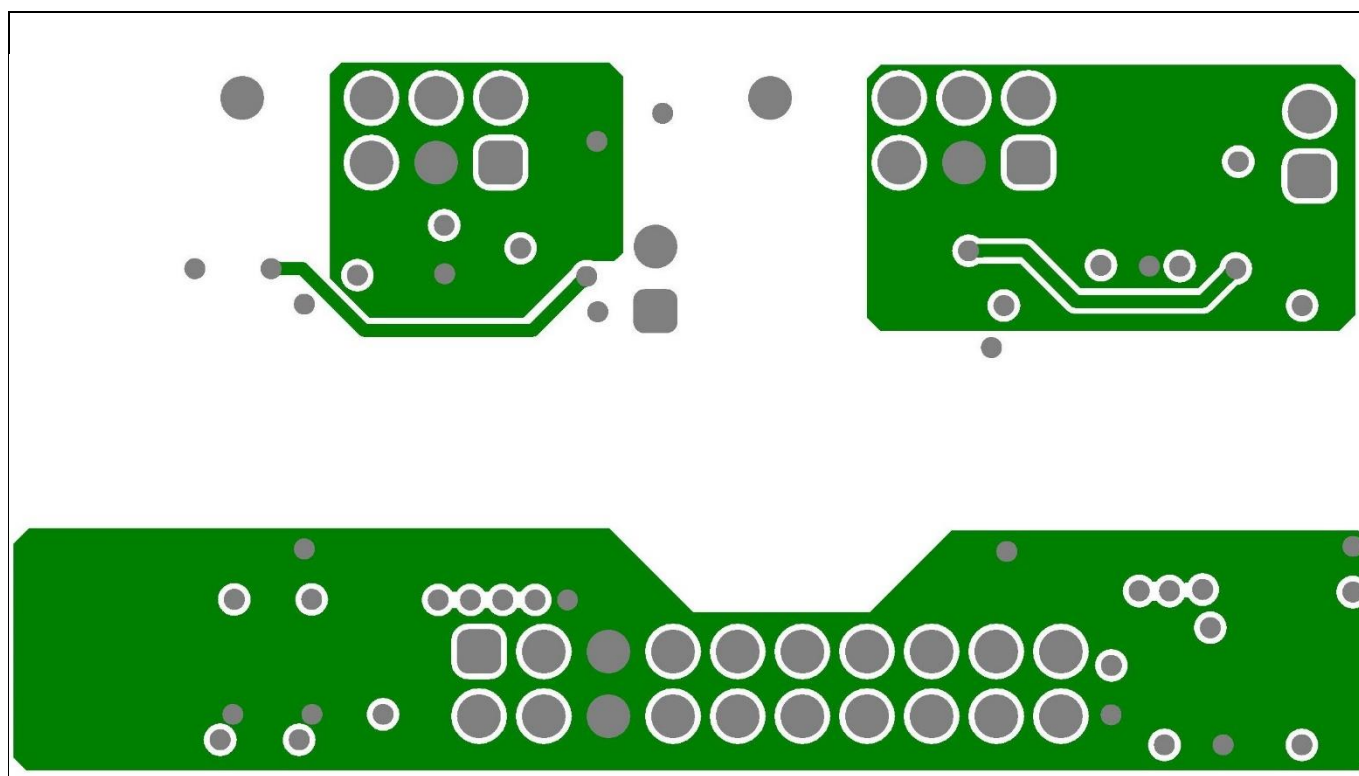


Figure 10 Layer 1 of EVAL-1ED020I12F2-DB

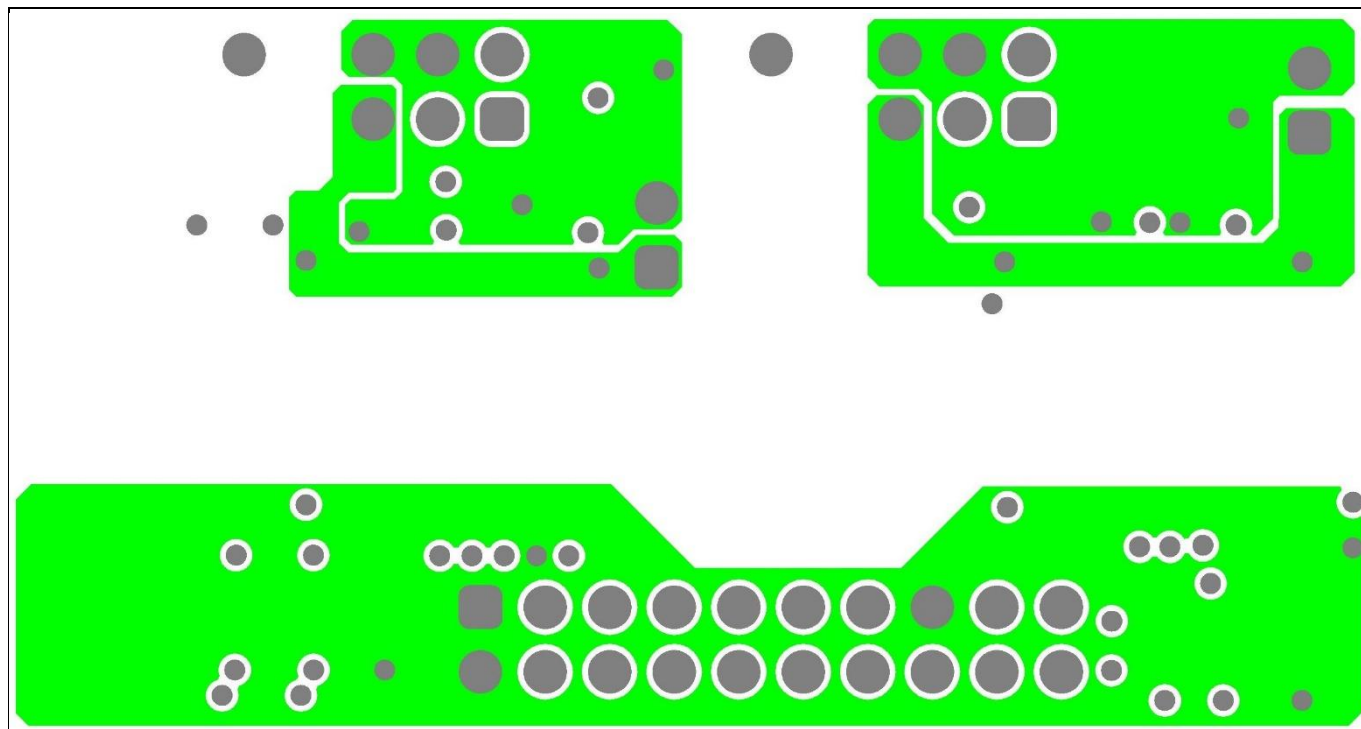


Figure 11 Layer 2 of EVAL-1ED020I12F2-DB

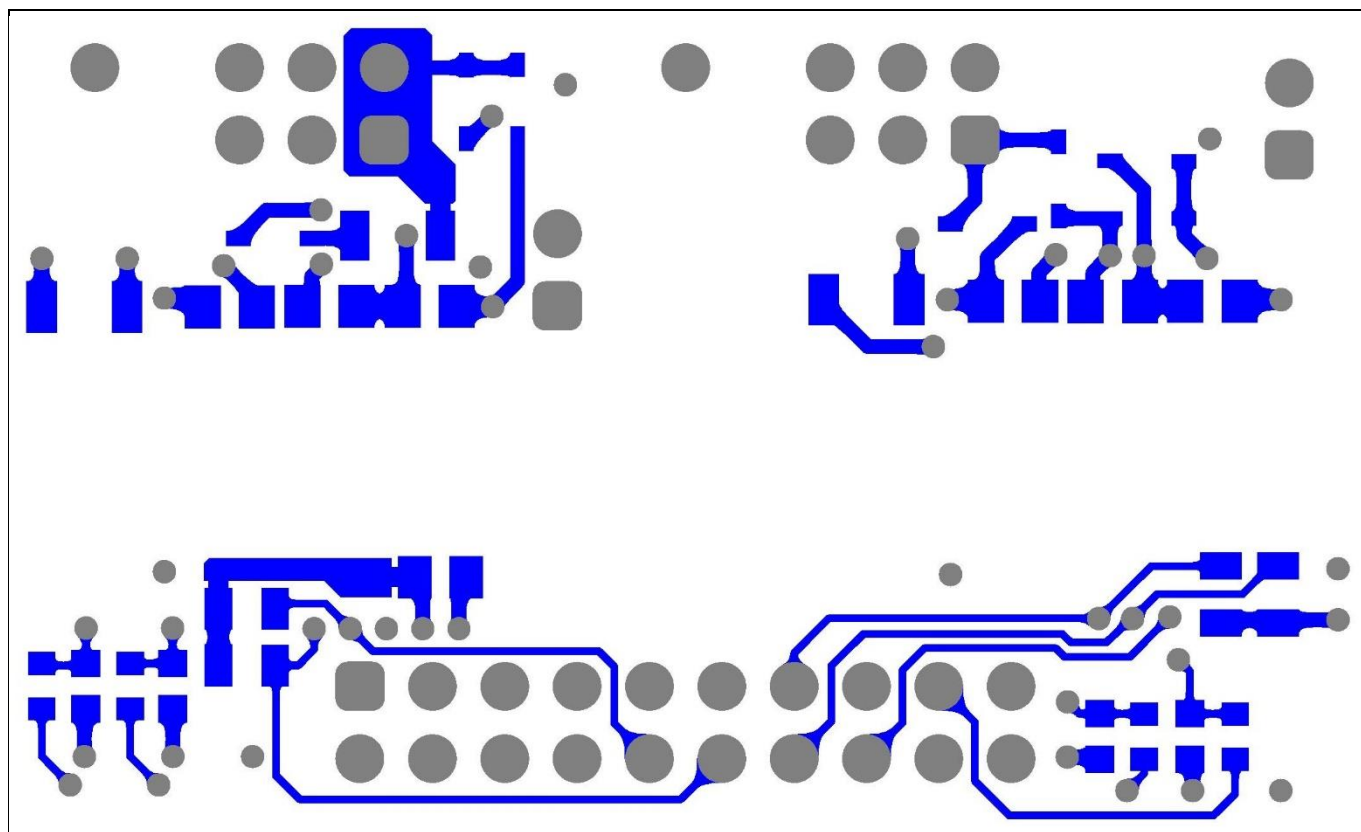


Figure 12 Bottom layer of EVAL-1ED020I12F2-DB

System design

3.3 Bill of material

The complete bill of material is available on the download section of the Infineon homepage. A log-in is required to download this material.

Table 4 BOM of the evaluation board EVAL-1ED020I12F2-DB

| comment | Ref Designator | Description | Manufacturer | Manufacturer P/N |
|-----------------|---|---|-----------------------|-----------------------|
| 1 uF | C1, C7 | Surface Mount Ceramic Capacitor Automotive Grade | AVX | 478-6357-2-ND |
| 4.7 uF | C2, C6, C8, C12, C13, C14 | TDK multilayer ceramic chip capacitor_Soft termination_Automotive grade_CGA serie | TDK Corporation | 445-181410-1-ND |
| 33 pF | C3, C9 | High temperature application CGA series | TDK Corporation | 445-12409-1-ND |
| 100 pF | C4, C5, C10, C11 | Surface Mount Multilayer Ceramic Chip Capacitor | Kemet | |
| BAT165 | D1, D2, D4, D5, D6, D7, D8, D10, D11, D12 | Medium Power AF Schottky Diode | Infineon Technologies | BAT165E6327HTSA1TR-ND |
| S3N | D3, D9 | General-Purpose Rectifier, VRRM 1200V | ON Semiconductor | S3NCT-ND |
| 4.7 k | R1, R7, R9, R15 | Standard Thick Film Chip Resistor | Vishay | |
| 9.1 k | R2, R10 | Standard Thick Film Chip Resistor | Vishay | |
| 0 R | R3, R6, R11, R14 | General Purpose Chip Resistor | Yageo | 311-0.0GRTR-ND |
| 0 R | R4, R12 | Solder Stability Chip Resistor | Bourns | CR0603-J/-000ELFTR-ND |
| 10 R | R5, R8, R13, R16 | General Purpose Chip Resistor | Yageo | |
| 1ED020I12-F2 | U1, U2 | Galvanically isolated single-channel IGBT driver provides protection features like desaturation protection, active Miller clamping and active shut down | Infineon Technologies | 1ED020I12F2XUMA1CT-ND |
| TSW-105-07-L-D | X200, X201 | Through hole .025" SQ Post Header, 2.54mm pitch, 10 pin, vertical, double row | Samtec | SAM1030-05-ND |
| HTSW-110-07-L-D | X202 | Hi -Temp Strip, Through hole .025" SQ Post | Samtec | SAM12659-ND |

System design

| comment | Ref Designator | Description | Manufacturer | Manufacturer P/N |
|----------------|----------------|--|--------------|------------------|
| | | Header, 2.54mm pitch, 20 pin, vertical, double row | | |
| TLW-102-05-G-S | X203, X204 | Through hole .025" SQ Post Header, 2.54mm pitch, 2 pin, vertical, single row | Samtec | SAM8736-ND |

3.4 Connector details

The following Tables 5, 6 and 7 list the respective signal assignments corresponding to the plug connections.

Table 5 Connector X202 (Primary side)

| PIN | Label | Function |
|-----|--------|-------------------------------------|
| 1 | VCC1 | Power supply primary side |
| 2 | VCC1 | Power supply primary side |
| 3 | nc | |
| 4 | nc | |
| 5 | GND_P | Ground primary side |
| 6 | GND_P | Ground primary side |
| 7 | IN+ T | Positive driver input IN+ high-side |
| 8 | IN- T | Negative driver input IN- high-side |
| 9 | /RST_T | Reset input high-side, low active |
| 10 | /FLT_T | Fault output high-side, low active |
| 11 | nc | |
| 12 | RDY_T | RDY output high-side |
| 13 | RDY_B | RDY output low-side |
| 14 | /FLT_B | Fault output low-side, low active |
| 15 | VCC1 | Power supply primary side |
| 16 | /RST_B | Reset input low side, low active |
| 17 | IN- B | Negative driver input IN- low-side |
| 18 | IN+ B | Positive driver input IN+ low-side |
| 19 | nc | |
| 20 | nc | |

System design

Table 6 Connector X200 (High-side power switch – secondary side)

| PIN | Label | Function |
|-----|-------------------|---|
| 1 | HS_Gate | Gate voltage high-side !! HIGH VOLTAGE!! |
| 2 | HS_Gate | Gate voltage high-side !! HIGH VOLTAGE!! |
| 3 | HS_VON (0..+20 V) | Positive power supply (VCC2) high-side !! HIGH VOLTAGE!! |
| 4 | HS_GND_SEC | Ground high-side secondary side !! HIGH VOLTAGE!! |
| 5 | HS_VOFF (0..-5 V) | Negative power supply (VEE2) high-side |
| 6 | HS_GND_SEC | Ground high-side secondary side !! HIGH VOLTAGE!! |
| 7 | | |
| 8 | | |
| 9 | | |
| 10 | HS_HV_VDC | Drain (collector) interface for DESAT high-side !! HIGH VOLTAGE!! |

Table 7 Connector X201 (Low-side power switch – secondary side)

| PIN | Label | Function |
|-----|---------------------|--|
| 1 | LS_Gate | Gate voltage low-side |
| 2 | LS_Gate | Gate voltage low-side |
| 3 | LS_VON (0..+20 V) | Positive power supply (VCC2) low-side |
| 4 | LS_GND_SEC | Ground low-side secondary side |
| 5 | LS_VOFF (0..-5 V) | Negative power supply (VEE2) high-side |
| 6 | LS_GND_SEC | Ground high-side secondary side |
| 7 | | |
| 8 | | |
| 9 | | |
| 10 | HV_Midpoint (phase) | Drain (collector) interface for DESAT low-side !! HIGH VOLTAGE!! |

4 System performance

In Chapter 4 some measurement results are introduced. These measurements are intended to demonstrate that the system is fully operational and that clear measurement data can be derived.

4.1 Short circuit measurements

Since the overcurrent or short-circuit protection is an important function of the gate driver IC 1ED020I12-F2, some measurements are presented here. Figure 13 illustrates the main functionality of the overcurrent shutdown using DESAT functionality.

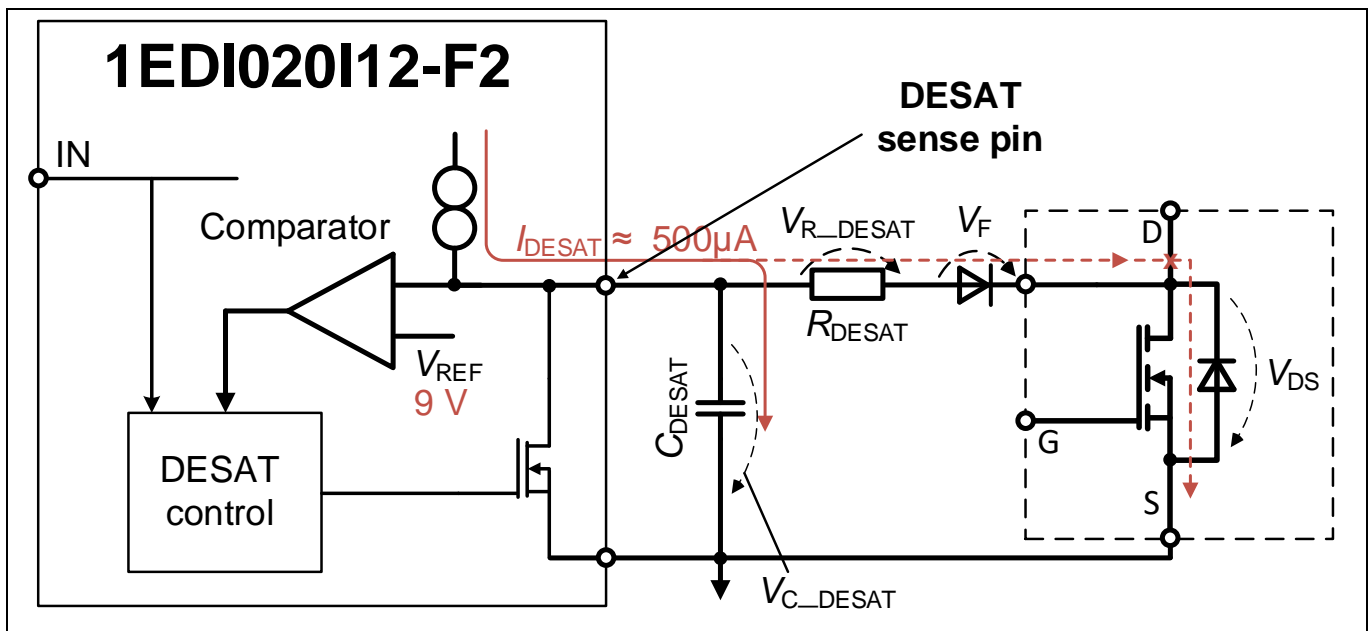


Figure 13 Circuitry for DESAT functionality

On the left-hand side of Figure 13, a section of the internal circuitry of the gate driver is shown schematically. The internal power source delivers a constant current of around 500 μA and is connected to the internal comparator and the DESAT pin. A charging capacitor C_{DESAT} , a resistor R_{DESAT} and a fast high voltage diode V_F with the smallest possible capacitance are connected to the external DESAT-sense pin as shown in Figure 13. The cathode of the high voltage diode is connected directly to the drain of the SiC MOSFET. This diode prevents the high voltage from reaching the gate driver.

The DESAT module only works when the driver is switched on, i.e. when the gate driver switches on the power switch via input “IN”. In this case, a so-called leading-edge blanking time (t_{DESATleb}) is expected, during which no action is taken. This represents a delay time, which ignores certain disturbances or oscillations caused by the switch-on process. Of course, no short circuit should be displayed here.

After that time, the capacitor is released and a part of the current from the internal current source charges the capacitor. Another part of the current flows through the resistor and the diode through the drain. In normal operation (no error case) an equilibrium is established. The voltage $V_{\text{C-DESAT}}$ can be calculated using Equation 2 from Figure 14, and should be significantly lower than 9 V.

If an error occurs, e.g. an excessively high current due to a short circuit, the voltage V_{DS} (from SiC MOSFET in this case) will increase. If the voltage at the drain is too high, the diode V_F closes and the internal current source will charge the capacitor C_{DESAT} only. If the voltage on the capacitor exceeds 9 V, the internal comparator will

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switch off the output of the driver latching. This means the switch stays off, no matter what happens at the “IN” input. The driver must be released again by RESET.

Due to the constant current of the internal current source, the charging time of the capacitor can be calculated using Equation 1 from Figure 14. It should be noted that any capacitance which is in some way connected to the DESAT pin (protection diodes, capacitances via layout, capacitance of high voltage diode V_F) must also be considered. For example, charges from the drain can also reach the capacitor V_{C_DESAT} through the capacitance of the diode V_F , and thus shorten the charging time.

$$t_{DESAT} = C_{DESAT} \cdot \frac{V_{REF} - V_{C_DESAT}}{I_{DESAT}} \quad \text{Equation 1}$$

$$V_{C_DESAT} = I_{DESAT} \cdot R_{DESAT} + V_F + V_{DS} \quad \text{Equation 2}$$

Figure 14 Equations to describe DESAT behavior

4.1.1 Example measurement 1: switching resistive load

Figure 15 illustrates the first example measurement. The load is a 47 Ω resistor in this case.

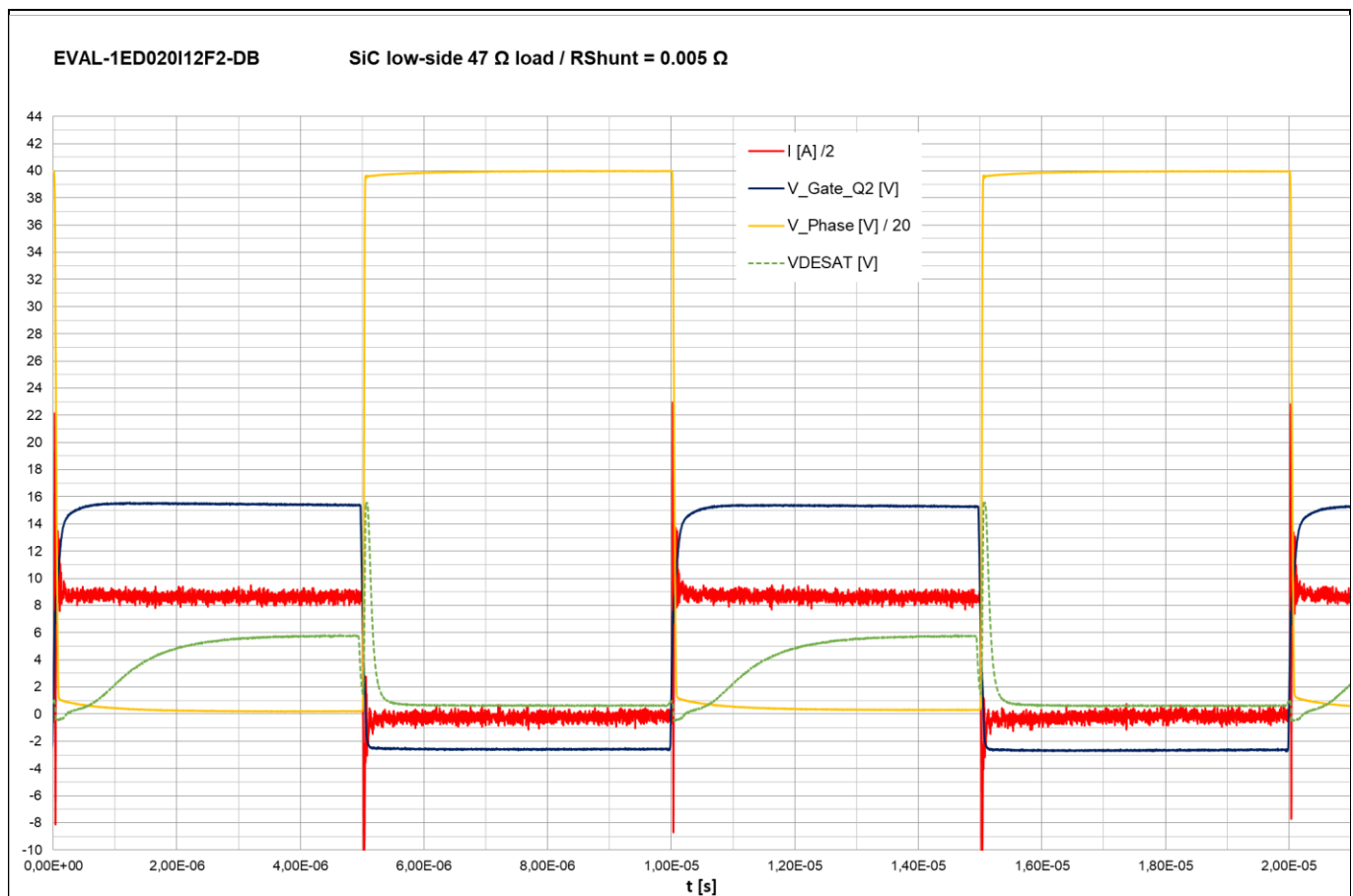


Figure 15 Switching resistive load according to figure 7

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Figure 15 shows how the measurement works with an ohmic load resistor in a low-side configuration. As soon as the gate voltage rises (blue line) to 15 V (switch-on process), the phase voltage (yellow line) falls to below 1 V, and the drain current (red line) of Q2 (or load current) increases to approximately 17 A. The DESAT voltage (green dashed line) rises to almost 6 V after the leading-edge blanking time.

The switch-off process begins with the falling edge of the gate voltage. The phase voltage increases to approximate 800 V, and the load current drops down to 0 A. The DESAT output switches off and discharges the DESAT capacitor. The short intermediate peak looks like a capacitive behavior of the diode V_F and the very high du/dt (drain voltage) of approximately 23.400 V/ μ s.

4.1.2 Example measurement 2: short circuit at low-side

The second measurement example is shown in Figure 16 to and demonstrates a short-circuit measurement in low-side configuration. In this case, the load as shown in Figure 7 is replaced by a short cable.

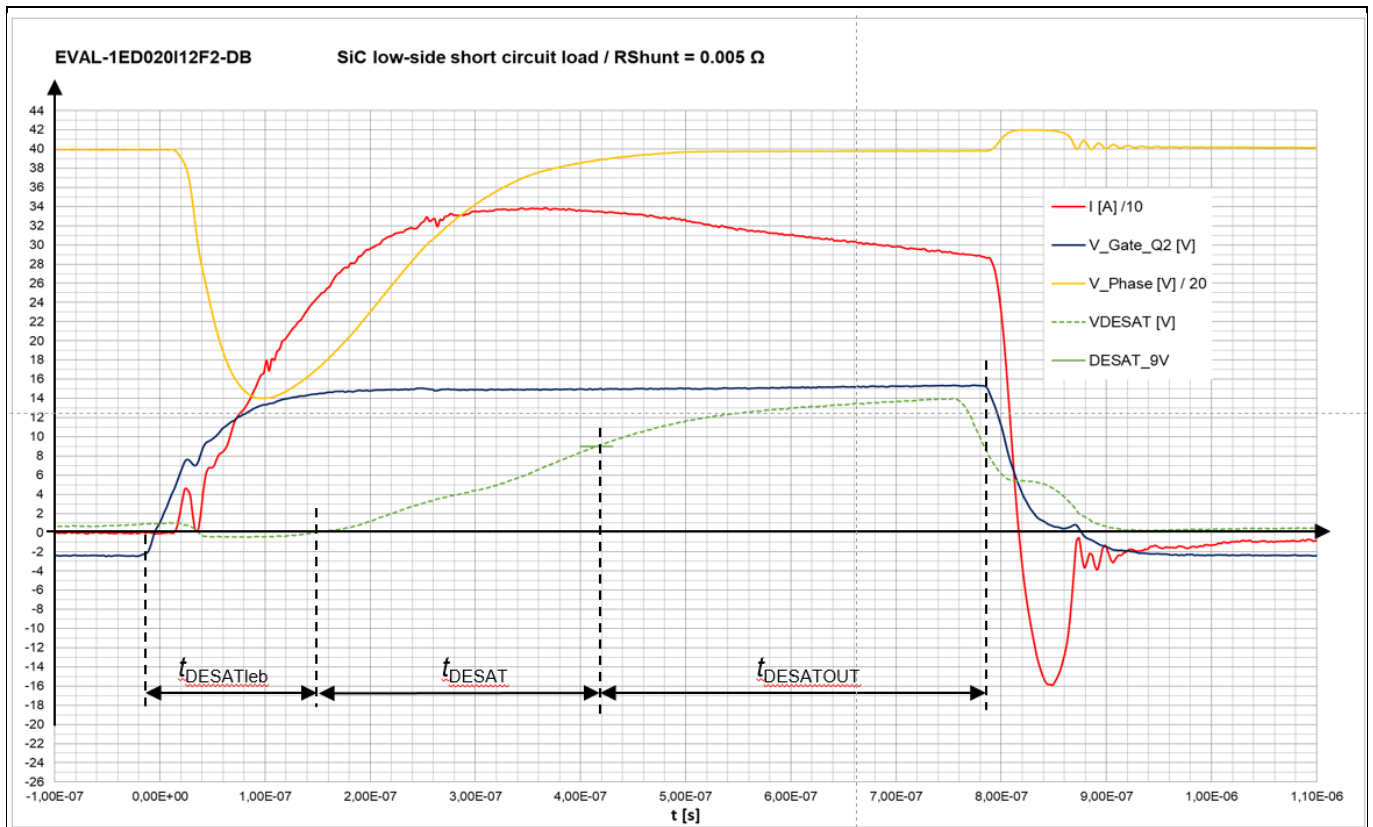


Figure 16 Short circuit measurement at low-side configuration

The switch-on process is the same as in the previous measurement. The only difference is that no resistor is connected in between. The pulse length at the input of the driver is the same at 5 μ s. As soon as the gate voltage increases, the load current increases rapidly up to approximately 330 A. Due to the very high current, the phase voltage briefly drops from around 800 V to 280 V, but recovers after several hundreds nanoseconds. It can be observed clearly that the current strength decreases slightly. This is related to the fact that the MOSFET heats up, and thus the internal resistance increases.

The voltage on the DESAT pin behaves as described in Chapter 4.1. After the leading-edge blanking time (t_{DESATleb}), the DESAT capacitor (C_{DESAT}) charges in time t_{DESAT} . From a DESAT voltage of 9 V, the driver is switched off internally. After another internal time delay (t_{DESATOUT}), the output switches off and the current begins to decrease. In this setup, the entire process takes about 780 ns.

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4.1.3 Example measurement 3: short circuit at high-side

For a short-circuit measurement in the high-side configuration, the external circuitry of the system must be changed slightly, see Figure 17.

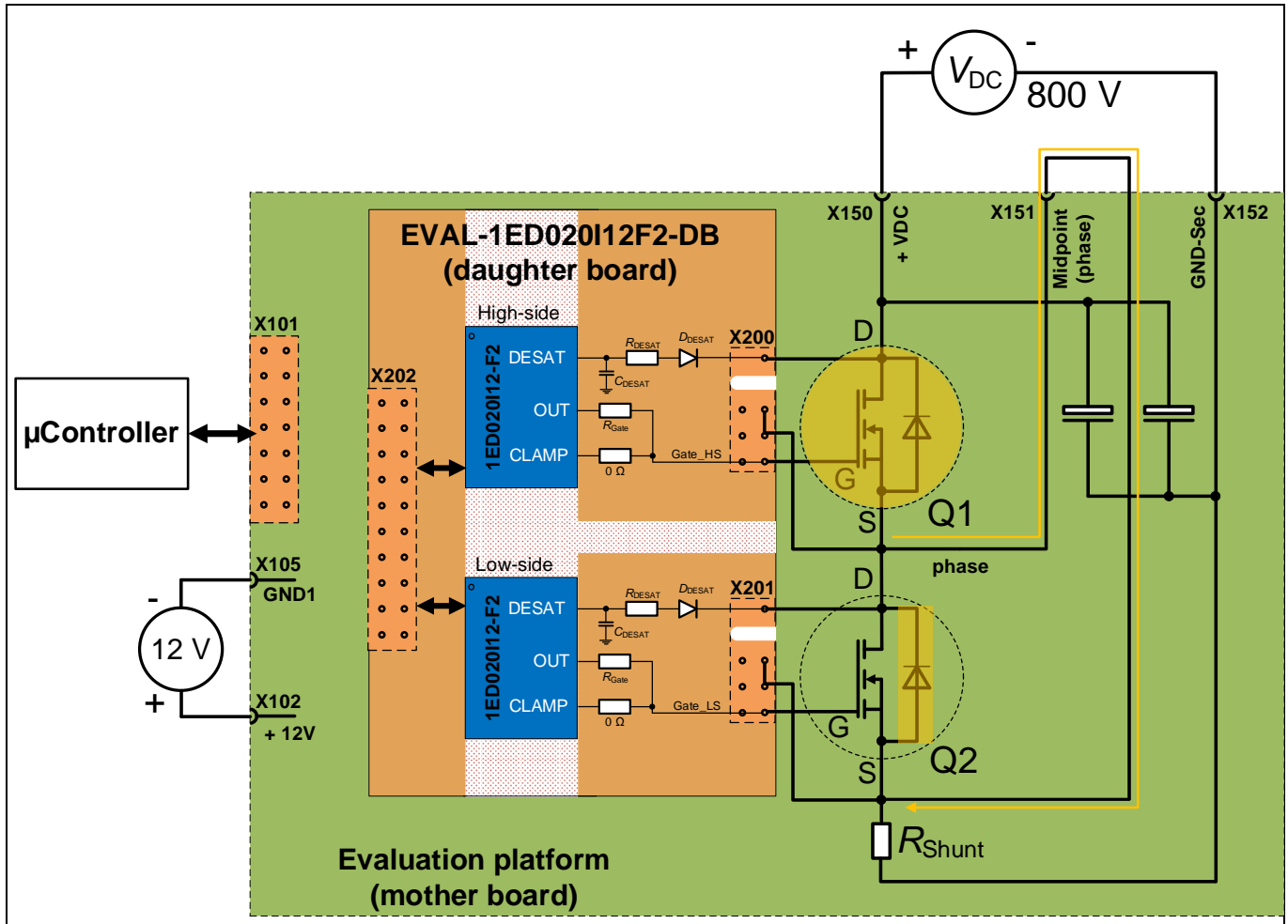


Figure 17 External circuit for high-side measurements

The first difference between the arrangements in Figure 7 and Figure 17 is that the switch Q1 is now the DUT. A short cable is connected accordingly between X151 and R_{Shunt} . The digital signals from the μ Controller should be connected in accordance with Table 5, so that the high-side driver is addressed. If everything is connected correctly, a diagram similar as in Figure 18 should be derived.

System performance

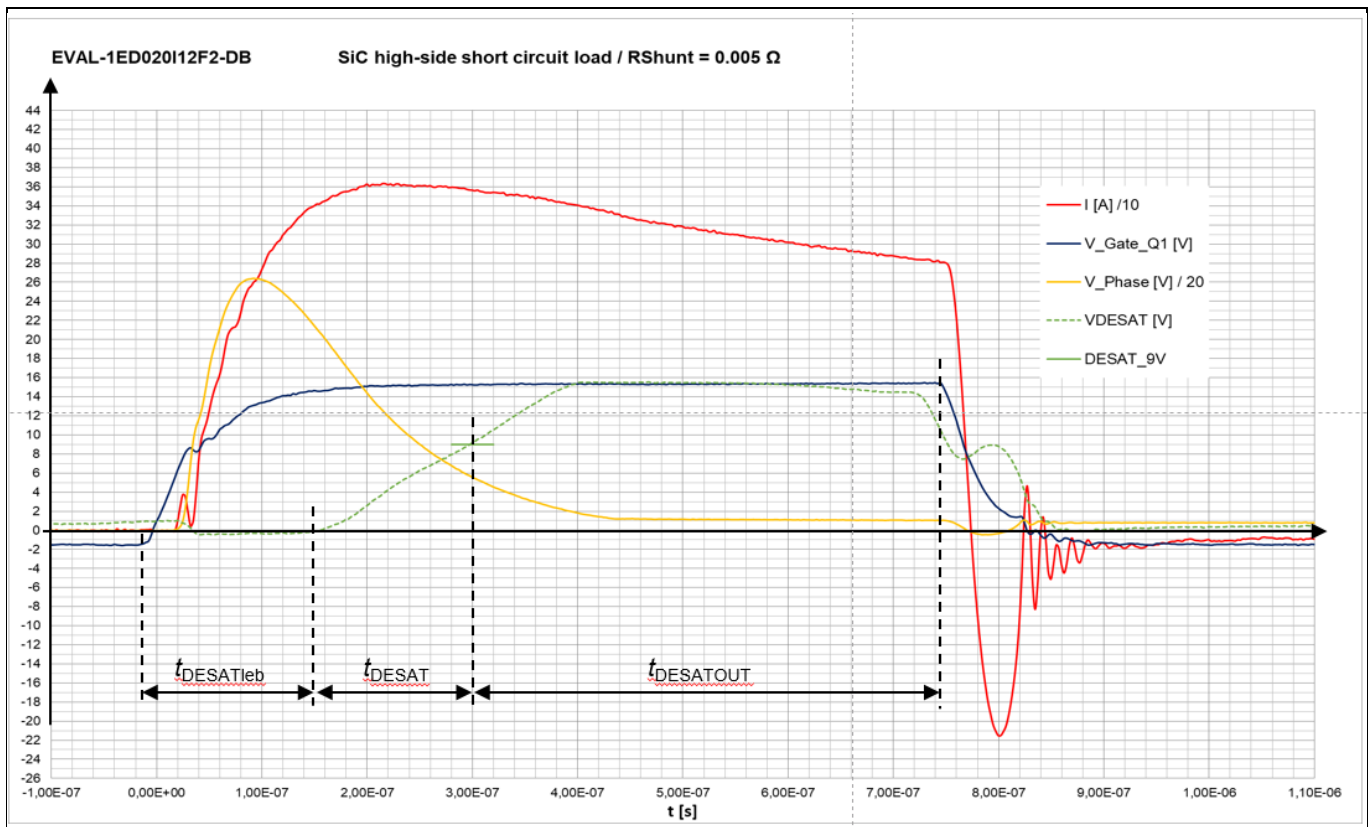


Figure 18 Short circuit measurement at high-side configuration

The measurement results shown in Figure 18 are similar to result in Chapter 4.1.2, Figure 16. The difference is that the phase voltage V_{Phase} increases from zero up to approximately 620 V when Q1 is switched on. Due to the steep rise and the high value of the current, the full DC voltage of 800 V is not reached. Shortly after the increase, the phase voltage drops down again due to the very high current value. Similar to the low-side measurement, the value of the current drops slightly due to the heating of the power switch, in this configuration SiC MOSFET Q1.

After approximately 760 ns, the output of the driver switches off.

5 References and appendices

5.1 Abbreviations and definitions

Table 8 Abbreviations

| Abbreviation | Meaning |
|---------------------|------------------------------|
| CE | Conformité Européenne |
| EMI | Electromagnetic interference |
| UL | Underwriters Laboratories |
| DUT | Device under test |

5.2 References

5.3 Additional information

Revision history**Revision history**

| Document version | Date of release | Description of changes |
|------------------|-----------------|---|
| Revision 1.0 | 2021-05-20 | Initial release |
| Revision 1.1 | 2021-05-25 | Change footnote (Revision 1.x instead of v 1.x), add revision history |
| | | |

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